

S/N 10/765,619

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al. Examiner: Asok K. Sarkar  
Serial No.: 10/765,619 Group Art Unit: 2891  
Filed: January 27, 2004 Docket: 1303.033US2  
Title: HIGH-QUALITY PRASEODYMIUM GATE DIELECTRICS (AS AMENDED)

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COMMUNICATION CONCERNING RELATED APPLICATION(S)

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P.O. Box 1450  
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
10/909959	August 2, 2004	1303.114US1	ATOMIC LAYER DEPOSITION OF ZIRCONIUM-DOPED TANTALUM OXIDE FILMS
10/931533	August 31, 2004	1303.119US1	ATOMIC LAYER DEPOSITED TITANIUM ALUMINUM OXIDE FILMS
10/926812	August 26, 2004	1303.121US1	RUTHENIUM GATE FOR A LANTHANIDE OXIDE DIELECTRIC LAYER
10/930167	August 31, 2004	1303.122US1	ATOMIC LAYER DEPOSITED LANTHANUM ALUMINUM OXIDE DIELECTRIC LAYER
11/010529	December 13, 2004	1303.126US1	ATOMIC LAYER DEPOSITED LANTHANUM HAFNIUM OXIDE DIELECTRICS
11/029757	January 5, 2005	1303.127US1	ATOMIC LAYER DEPOSITED HAFNIUM TANTALUM OXIDE DIELECTRICS
11/010766	December 13, 2004	1303.129US1	HYBRID ALD-CVD OF Pr <sub>x</sub> YO <sub>y</sub> /ZrO <sub>2</sub> FILMS AS GATE DIELECTRICS
11/063717	February	1303.134US1	ATOMIC LAYER DEPOSITION OF

## COMMUNICATION CONCERNING RELATED APPLICATIONS

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	23, 2005		Hf <sub>3</sub> N <sub>4</sub> /HfO <sub>2</sub> FILMS AS GATE DIELECTRICS
11/092072	March 29, 2005	1303.135US1	ALD OF AMORPHOUS LANTHANIDE DOPED TIO <sub>2</sub> FILMS
11/093104	March 29, 2005	1303.136US1	ATOMIC LAYER DEPOSITED TITANIUM SILICON OXIDE FILMS
11/117121	April 28, 2005	1303.138US1	ATOMIC LAYER DEPOSITED ZIRCONIUM SILICON OXIDE FILMS
11/117125	April 28, 2005	1303.139US1	ATOMIC LAYER DEPOSITION OF A RUTHENIUM LAYER TO A LANTHANIDE OXIDE DIELECTRIC LAYER
11/084968	March 21, 2005	1303.083US2	Zr-Sn-Ti-O FILMS
11/148505	June 9, 2005	1303.061US2	ATOMIC LAYER DEPOSITED NANOLAMINATES OF HfO <sub>2</sub> /ZrO <sub>2</sub> FILMS AS GATE DIELECTRICS

Continuations and divisionals may be later filed on the cases listed above, or cited to the Examiner in any previous Communication Concerning Related Applications. Applicant requests that the Examiner review all continuations and divisionals of the above-listed or previously-cited patent applications before allowing the claims of the present patent application.

Respectfully submitted,  
KIE Y. AHN ET AL.

By Applicants' Representatives,  
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Date 20 June 2005

By

David R. Cochran  
Reg. No. 46,632



CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Mail Stop AF, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 20 day of June, 2005.

Name KACIA LEE

Signature Kacia Lee

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie. Y. Ahn et al.

Title: HIGH-QUALITY PRASEODYMIUM GATE DIELECTRICS (As Amended)

Docket No.: 1303.033US2

Serial No.: 10/765,619

Filed: January 27, 2004

Due Date: July 19, 2005

Examiner: Asok K Sarkar

Group Art Unit: 2891



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Alexandria, VA 22313-1450

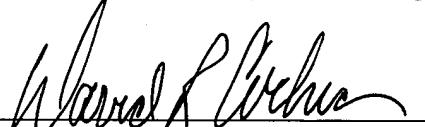
We are transmitting herewith the following attached items (as indicated with an "X"):

- A return postcard.
- An Amendment and Response Under 37 CFR 1.116--Expedited Procedure (13 Pages).
- A Communication Concerning Related Applications (2 pgs.).

If not provided for in a separate paper filed herewith, Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

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By:   
Atty: David R. Cochran  
Reg. No. 46,632

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(GENERAL)